

Diode, Wechselrichter / Diode, Inverter

Höchstzulässige Werte / Maximum Rated Values

Periodische Spitzensperrspannung Repetitive peak reverse voltage	$T_{vj} = 25^{\circ}\text{C}$	V_{RRM}	1200	V
Dauergleichstrom Continuous DC forward current		I_F	35	A
Periodischer Spitzenstrom Repetitive peak forward current	$t_p = 1\text{ ms}$	I_{FRM}	70	A
Grenzlastintegral I^2t - value	$V_R = 0\text{ V}, t_p = 10\text{ ms}, T_{vj} = 125^{\circ}\text{C}$	I^2t	240	A^2s

Charakteristische Werte / Characteristic Values

			min.	typ.	max.	
Durchlassspannung Forward voltage	$I_F = 35\text{ A}, V_{GE} = 0\text{ V}$ $I_F = 35\text{ A}, V_{GE} = 0\text{ V}$ $I_F = 35\text{ A}, V_{GE} = 0\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	V_F	1,70 1,65 1,65	2,15	V V V
Rückstromspitze Peak reverse recovery current	$I_F = 35\text{ A}, -di_F/dt = 1100\text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$ $V_R = 600\text{ V}$ $V_{GE} = -15\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	I_{RM}	35,0 39,0 40,0		A A A
Sperrverzögerungsladung Recovered charge	$I_F = 35\text{ A}, -di_F/dt = 1100\text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$ $V_R = 600\text{ V}$ $V_{GE} = -15\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	Q_r	3,40 6,30 7,20		μC μC μC
Abschaltenergie pro Puls Reverse recovery energy	$I_F = 35\text{ A}, -di_F/dt = 1100\text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$ $V_R = 600\text{ V}$ $V_{GE} = -15\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	E_{rec}	1,10 2,20 2,50		mJ mJ mJ
Wärmewiderstand, Chip bis Kühlkörper Thermal resistance, junction to heatsink	pro Diode / per diode valid with IFX pre-applied thermal interface material		R_{thJH}		1,07	K/W
Temperatur im Schaltbetrieb Temperature under switching conditions			$T_{vj\text{ op}}$	-40	150	$^{\circ}\text{C}$

Diode, Gleichrichter / Diode, Rectifier

Höchstzulässige Werte / Maximum Rated Values

Periodische Spitzensperrspannung Repetitive peak reverse voltage	$T_{vj} = 25^{\circ}\text{C}$	V_{RRM}	1600	V
Durchlassstrom Grenzeffektivwert pro Chip Maximum RMS forward current per chip	$T_H = 70^{\circ}\text{C}$	I_{FRMSM}	70	A
Gleichrichter Ausgang Grenzeffektivstrom Maximum RMS current at rectifier output	$T_H = 70^{\circ}\text{C}$	I_{RMSM}	80	A
Stoßstrom Grenzwert Surge forward current	$t_p = 10\text{ ms}, T_{vj} = 25^{\circ}\text{C}$ $t_p = 10\text{ ms}, T_{vj} = 150^{\circ}\text{C}$	I_{FSM}	450 370	A A
Grenzlastintegral I^2t - value	$t_p = 10\text{ ms}, T_{vj} = 25^{\circ}\text{C}$ $t_p = 10\text{ ms}, T_{vj} = 150^{\circ}\text{C}$	I^2t	1000 685	A^2s A^2s

Charakteristische Werte / Characteristic Values

			min.	typ.	max.	
Durchlassspannung Forward voltage	$T_{vj} = 150^{\circ}\text{C}, I_F = 35\text{ A}$	V_F		0,95		V
Sperrstrom Reverse current	$T_{vj} = 150^{\circ}\text{C}, V_R = 1600\text{ V}$	I_R		1,00		mA
Wärmewiderstand, Chip bis Kühlkörper Thermal resistance, junction to heatsink	pro Diode / per diode valid with IFX pre-applied thermal interface material		R_{thJH}		0,999	K/W
Temperatur im Schaltbetrieb Temperature under switching conditions			$T_{vj\text{ op}}$	-40	150	$^{\circ}\text{C}$

IGBT, Brems-Chopper / IGBT, Brake-Chopper Höchstzulässige Werte / Maximum Rated Values

Kollektor-Emitter-Sperrspannung Collector-emitter voltage	$T_{vj} = 25^{\circ}\text{C}$	V_{CES}	1200	V
Kollektor-Dauergleichstrom Continuous DC collector current	$T_H = 100^{\circ}\text{C}, T_{vj\max} = 175^{\circ}\text{C}$	$I_{C\text{nom}}$	25	A
Periodischer Kollektor-Spitzenstrom Repetitive peak collector current	$t_P = 1\text{ ms}$	I_{CRM}	50	A
Gate-Emitter-Spitzenspannung Gate-emitter peak voltage		V_{GES}	+/-20	V

Charakteristische Werte / Characteristic Values

			min.	typ.	max.		
Kollektor-Emitter-Sättigungsspannung Collector-emitter saturation voltage	$I_C = 25\text{ A}, V_{GE} = 15\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$	$V_{CE\text{sat}}$	1,85	2,15	V	
	$I_C = 25\text{ A}, V_{GE} = 15\text{ V}$	$T_{vj} = 125^{\circ}\text{C}$		2,15		V	
	$I_C = 25\text{ A}, V_{GE} = 15\text{ V}$	$T_{vj} = 150^{\circ}\text{C}$		2,25		V	
Gate-Schwellenspannung Gate threshold voltage	$I_C = 0,80\text{ mA}, V_{CE} = V_{GE}, T_{vj} = 25^{\circ}\text{C}$		V_{GEth}	5,20	5,80	6,40	V
Gateladung Gate charge	$V_{GE} = -15\text{ V} \dots +15\text{ V}$		Q_G		0,20		μC
Interner Gatewiderstand Internal gate resistor	$T_{vj} = 25^{\circ}\text{C}$		R_{Gint}		0,0		Ω
Eingangskapazität Input capacitance	$f = 1\text{ MHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}$		C_{ies}		1,45		nF
Rückwirkungskapazität Reverse transfer capacitance	$f = 1\text{ MHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}$		C_{res}		0,05		nF
Kollektor-Emitter-Reststrom Collector-emitter cut-off current	$V_{CE} = 1200\text{ V}, V_{GE} = 0\text{ V}, T_{vj} = 25^{\circ}\text{C}$		I_{CES}			1,0	mA
Gate-Emitter-Reststrom Gate-emitter leakage current	$V_{CE} = 0\text{ V}, V_{GE} = 20\text{ V}, T_{vj} = 25^{\circ}\text{C}$		I_{GES}			100	nA
Einschaltverzögerungszeit, induktive Last Turn-on delay time, inductive load	$I_C = 25\text{ A}, V_{CE} = 600\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{Gon} = 37\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$	t_{don}	0,05		μs	
		$T_{vj} = 125^{\circ}\text{C}$		0,06		μs	
		$T_{vj} = 150^{\circ}\text{C}$		0,06		μs	
Anstiegszeit, induktive Last Rise time, inductive load	$I_C = 25\text{ A}, V_{CE} = 600\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{Gon} = 37\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$	t_r	0,03		μs	
		$T_{vj} = 125^{\circ}\text{C}$		0,04		μs	
		$T_{vj} = 150^{\circ}\text{C}$		0,05		μs	
Abschaltverzögerungszeit, induktive Last Turn-off delay time, inductive load	$I_C = 25\text{ A}, V_{CE} = 600\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{Goff} = 37\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$	t_{doff}	0,34		μs	
		$T_{vj} = 125^{\circ}\text{C}$		0,43		μs	
		$T_{vj} = 150^{\circ}\text{C}$		0,45		μs	
Fallzeit, induktive Last Fall time, inductive load	$I_C = 25\text{ A}, V_{CE} = 600\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{Goff} = 37\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$	t_f	0,05		μs	
		$T_{vj} = 125^{\circ}\text{C}$		0,07		μs	
		$T_{vj} = 150^{\circ}\text{C}$		0,08		μs	
Einschaltverlustenergie pro Puls Turn-on energy loss per pulse	$I_C = 25\text{ A}, V_{CE} = 600\text{ V}, L_S = 20\text{ nH}$ $V_{GE} = \pm 15\text{ V}$ $R_{Gon} = 37\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$	E_{on}	2,00		mJ	
		$T_{vj} = 125^{\circ}\text{C}$		2,65		mJ	
		$T_{vj} = 150^{\circ}\text{C}$		2,90		mJ	
Abschaltverlustenergie pro Puls Turn-off energy loss per pulse	$I_C = 25\text{ A}, V_{CE} = 600\text{ V}, L_S = 20\text{ nH}$ $V_{GE} = \pm 15\text{ V}$ $R_{Goff} = 37\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$	E_{off}	1,40		mJ	
		$T_{vj} = 125^{\circ}\text{C}$		2,20		mJ	
		$T_{vj} = 150^{\circ}\text{C}$		2,40		mJ	
Kurzschlußverhalten SC data	$V_{GE} \leq 15\text{ V}, V_{CC} = 800\text{ V}$ $V_{CE\text{max}} = V_{CES} - L_{SCE} \cdot di/dt$	$t_P \leq 10\ \mu\text{s}, T_{vj} = 150^{\circ}\text{C}$	I_{SC}		90		A
Wärmewiderstand, Chip bis Kühlkörper Thermal resistance, junction to heatsink	pro IGBT / per IGBT valid with IFX pre-applied thermal interface material		R_{thJH}			0,959	K/W
Temperatur im Schaltbetrieb Temperature under switching conditions			$T_{vj\text{op}}$	-40		150	$^{\circ}\text{C}$